

## METHOD FOR FORMING HYBRID DEVICE GATES

### ABSTRACT

A method for forming self-aligned contact devices in a core region of a  
5 semiconductor substrate and non-self-aligned contact devices in a non-core region of  
the semiconductor substrate is disclosed in which a single gate film stack is used for  
forming gate structures in both the core region and in the non-core region. A dielectric  
layer is formed over a semiconductor substrate and a gate film stack is formed over the  
dielectric layer. The gate film stack is then patterned so as to form gate structures  
10 within both the core region and the non-core region.